

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA966

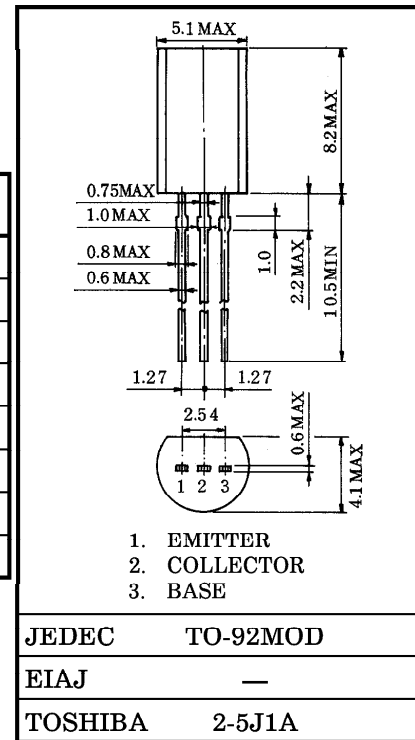
AUDIO POWER AMPLIFIER APPLICATIONS.

Unit in mm

- Complementary to 2SC2236 and 3Watts Output Applications.

MAXIMUM RATINGS (Ta = 25°C)

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|-----------------------------|------------------|---------|------|
| Collector-Base Voltage | V _{CB0} | -30 | V |
| Collector-Emitter Voltage | V _{CEO} | -30 | V |
| Emitter-Base Voltage | V _{EBO} | -5 | V |
| Collector Current | I _C | -1.5 | A |
| Emitter Current | I _E | 1.5 | A |
| Collector Power Dissipation | P _C | 900 | mW |
| Junction Temperature | T _j | 150 | °C |
| Storage Temperature Range | T _{stg} | -55~150 | °C |



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Weight : 0.36g

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|--------------------------------------|---------------------------|--|------|------|------|------|
| Collector Cut-off Current | I _{CBO} | V _{CB} = -30V, I _E = 0 | — | — | -100 | nA |
| Emitter Cut-off Current | I _{EBO} | V _{EB} = -5V, I _C = 0 | — | — | -100 | nA |
| Collector-Emitter Breakdown Voltage | V _{(BR)CEO} | I _C = -10mA, I _B = 0 | -30 | — | — | V |
| Emitter-Base Breakdown Voltage | V _{(BR)EBO} | I _E = -1mA, I _C = 0 | -5 | — | — | V |
| DC Current Gain | h _{FE} (Note) | V _{CE} = -2V, I _C = -500mA | 100 | — | 320 | |
| Collector-Emitter Saturation Voltage | V _{CE(sat)} | I _C = -1.5A, I _B = -0.03A | — | — | -2.0 | V |
| Base-Emitter Voltage | V _{BE} | V _{CE} = -2V, I _C = -500mA | — | — | -1.0 | V |
| Transition Frequency | f _T | V _{CE} = -2V, I _C = -500mA | — | 120 | — | MHz |
| Collector Output Capacitance | C _{ob} | V _{CB} = -10V, I _E = 0, f = 1MHz | — | — | 30 | pF |

Note : h_{FE} Classification O : 100~200, Y : 160~320

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